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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	1152
Number of Logic Elements/Cells	11520
Total RAM Bits	147456
Number of I/O	152
Number of Gates	728000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k300eqi240-2x

Table 2. Additional APEX 20K Device Features Note (1)

Feature	EP20K300E	EP20K400	EP20K400E	EP20K600E	EP20K1000E	EP20K1500E
Maximum system gates	728,000	1,052,000	1,052,000	1,537,000	1,772,000	2,392,000
Typical gates	300,000	400,000	400,000	600,000	1,000,000	1,500,000
LEs	11,520	16,640	16,640	24,320	38,400	51,840
ESBs	72	104	104	152	160	216
Maximum RAM bits	147,456	212,992	212,992	311,296	327,680	442,368
Maximum macrocells	1,152	1,664	1,664	2,432	2,560	3,456
Maximum user I/O pins	408	502	488	588	708	808

Note to Tables 1 and 2:

(1) The embedded IEEE Std. 1149.1 Joint Test Action Group (JTAG) boundary-scan circuitry contributes up to 57,000 additional gates.

Additional Features

- Designed for low-power operation
  - 1.8-V and 2.5-V supply voltage (see Table 3)
  - MultiVolt™ I/O interface support to interface with 1.8-V, 2.5-V, 3.3-V, and 5.0-V devices (see Table 3)
  - ESB offering programmable power-saving mode

Table 3. APEX 20K Supply Voltages

Feature	Device	
	EP20K100 EP20K200 EP20K400	EP20K30E EP20K60E EP20K100E EP20K160E EP20K200E EP20K300E EP20K400E EP20K600E EP20K1000E EP20K1500E
Internal supply voltage (V_{CCINT})	2.5 V	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	2.5 V, 3.3 V, 5.0 V	1.8 V, 2.5 V, 3.3 V, 5.0 V (1)

Note to Table 3:

(1) APEX 20KE devices can be 5.0-V tolerant by using an external resistor.

APEX 20K devices provide two dedicated clock pins and four dedicated input pins that drive register control inputs. These signals ensure efficient distribution of high-speed, low-skew control signals. These signals use dedicated routing channels to provide short delays and low skews. Four of the dedicated inputs drive four global signals. These four global signals can also be driven by internal logic, providing an ideal solution for a clock divider or internally generated asynchronous clear signals with high fan-out. The dedicated clock pins featured on the APEX 20K devices can also feed logic. The devices also feature ClockLock and ClockBoost clock management circuitry. APEX 20KE devices provide two additional dedicated clock pins, for a total of four dedicated clock pins.

MegaLAB Structure

APEX 20K devices are constructed from a series of MegaLAB™ structures. Each MegaLAB structure contains a group of logic array blocks (LABs), one ESB, and a MegaLAB interconnect, which routes signals within the MegaLAB structure. The EP20K30E device has 10 LABs, EP20K60E through EP20K600E devices have 16 LABs, and the EP20K1000E and EP20K1500E devices have 24 LABs. Signals are routed between MegaLAB structures and I/O pins via the FastTrack Interconnect. In addition, edge LABs can be driven by I/O pins through the local interconnect. Figure 2 shows the MegaLAB structure.

Figure 2. MegaLAB Structure

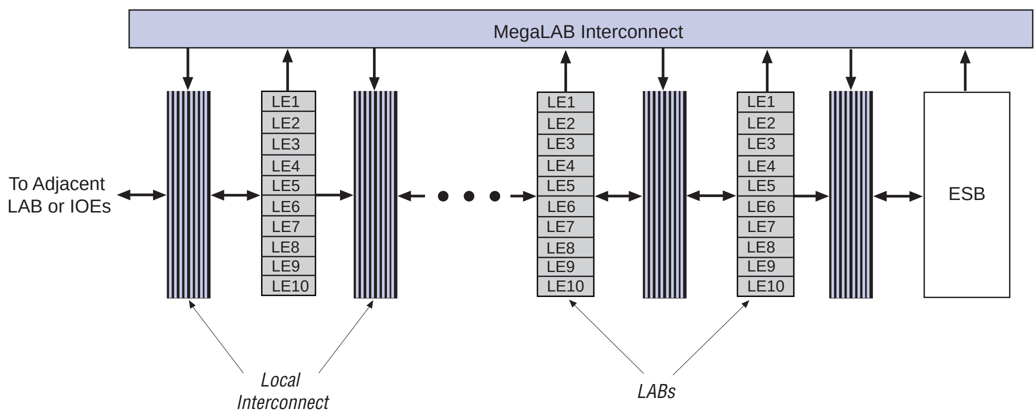
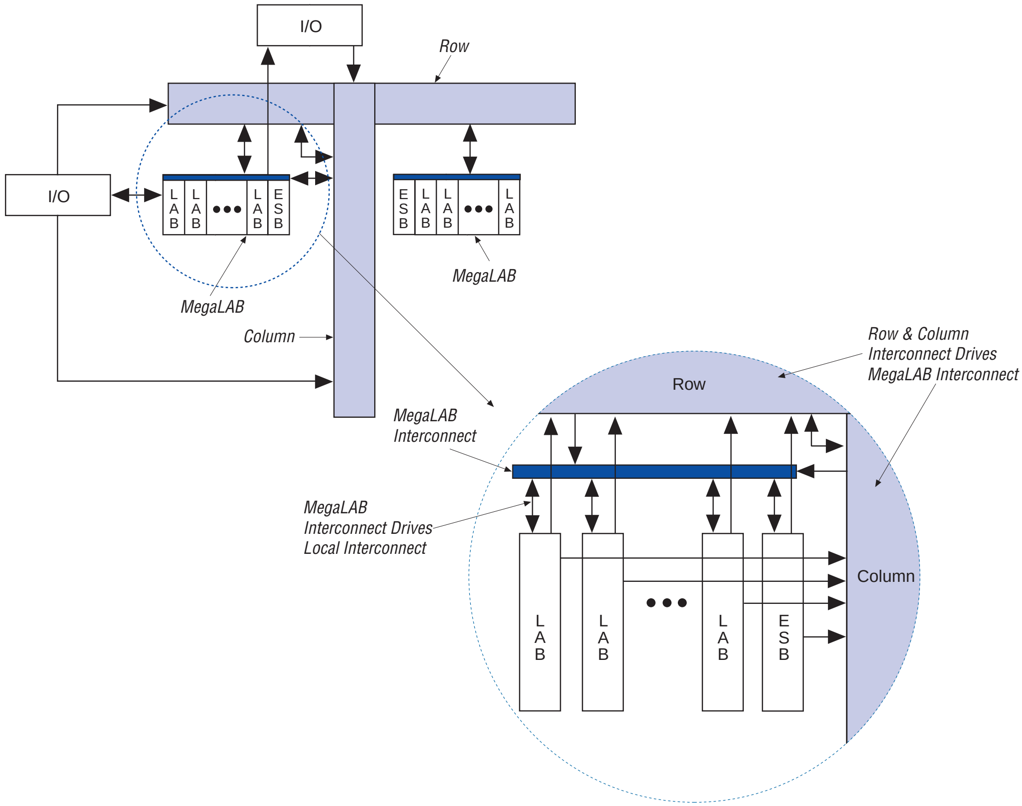


Figure 10. FastTrack Connection to Local Interconnect



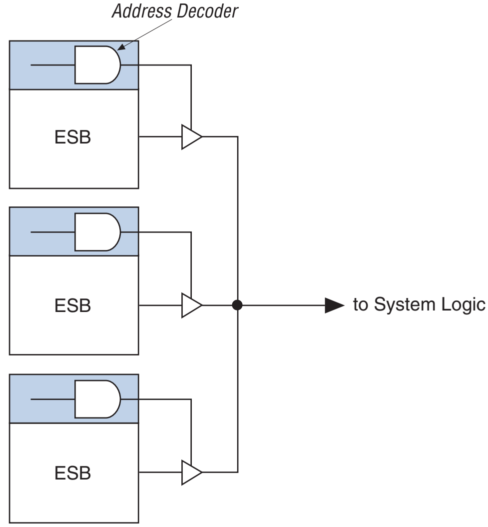
ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the MegaLAB or FastTrack Interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the MegaLAB and FastTrack Interconnect. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes: 128 × 16, 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two 128 × 16 RAM blocks can be combined to form a 128 × 32 RAM block, and two 512 × 4 RAM blocks can be combined to form a 512 × 8 RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

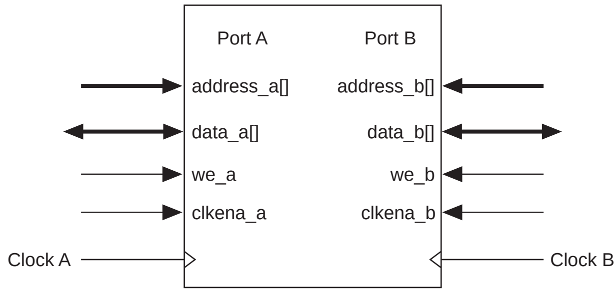
To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack Interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.

Figure 18. Deep Memory Block Implemented with Multiple ESBs



The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two or four ESBs are used to support two simultaneous reads or writes. This functionality is shown in Figure 19.

Figure 19. APEX 20K ESB Implementing Dual-Port RAM



Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20K ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20K device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20K IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times, or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The Quartus II software Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20K IOE offers one output enable per pin, the Quartus II software Compiler can emulate open-drain operation efficiently.

The APEX 20K IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

APEX 20KE devices include an enhanced IOE, which drives the FastRow interconnect. The FastRow interconnect connects a column I/O pin directly to the LAB local interconnect within two MegaLAB structures. This feature provides fast setup times for pins that drive high fan-outs with complex logic, such as PCI designs. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The APEX 20KE IOE also includes direct support for open-drain operation, giving faster clock-to-output for open-drain signals. Some programmable delays in the APEX 20KE IOE offer multiple levels of delay to fine-tune setup and hold time requirements. The Quartus II software compiler can set these delays automatically to minimize setup time while providing a zero hold time.

Table 11 describes the APEX 20KE programmable delays and their logic options in the Quartus II software.

Table 11. APEX 20KE Programmable Delay Chains

Programmable Delays	Quartus II Logic Option
Input Pin to Core Delay	Decrease input delay to internal cells
Input Pin to Input Register Delay	Decrease input delay to input registers
Core to Output Register Delay	Decrease input delay to output register
Output Register t_{CO} Delay	Increase delay to output pin
Clock Enable Delay	Increase clock enable delay

The register in the APEX 20KE IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. Figure 26 shows how fast bidirectional I/O pins are implemented in APEX 20KE devices. This feature is useful for cases where the APEX 20KE device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

Each IOE drives a row, column, MegaLAB, or local interconnect when used as an input or bidirectional pin. A row IOE can drive a local, MegaLAB, row, and column interconnect; a column IOE can drive the column interconnect. Figure 27 shows how a row IOE connects to the interconnect.

Figure 27. Row IOE Connection to the Interconnect

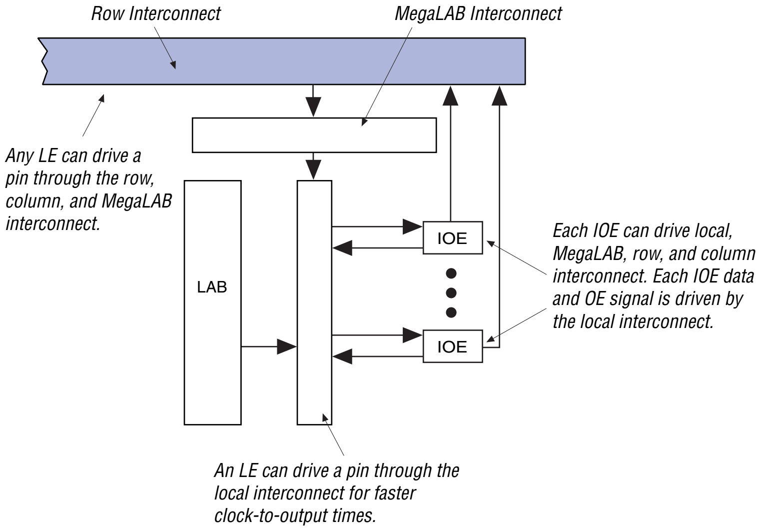
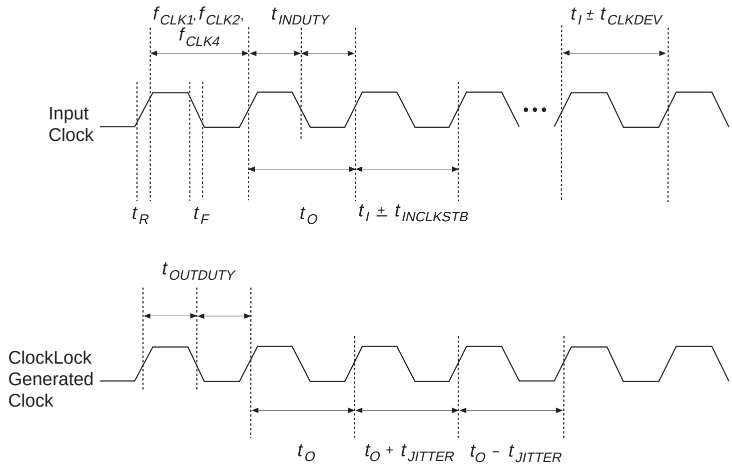


Figure 30. Specifications for the Incoming & Generated Clocks *Note (1)*



Note to Figure 30:

(1) The tI parameter refers to the nominal input clock period; the tO parameter refers to the nominal output clock period.

Table 15 summarizes the APEX 20K ClockLock and ClockBoost parameters for -1 speed-grade devices.

Table 15. APEX 20K ClockLock & ClockBoost Parameters for -1 Speed-Grade Devices (Part 1 of 2)

Symbol	Parameter	Min	Max	Unit
f_{OUT}	Output frequency	25	180	MHz
f_{CLK1} (1)	Input clock frequency (ClockBoost clock multiplication factor equals 1)	25	180 (1)	MHz
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16	90	MHz
f_{CLK4}	Input clock frequency (ClockBoost clock multiplication factor equals 4)	10	48	MHz
$t_{OUTDUTY}$	Duty cycle for ClockLock/ClockBoost-generated clock	40	60	%
f_{CLKDEV}	Input deviation from user specification in the Quartus II software (ClockBoost clock multiplication factor equals 1) (2)		25,000 (3)	PPM
t_R	Input rise time		5	ns
t_F	Input fall time		5	ns
t_{LOCK}	Time required for ClockLock/ClockBoost to acquire lock (4)		10	µs

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(11)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(11)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(11)*			0.7	V
I_I	Input pin leakage current	V_I = 5.75 to –0.5 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.75 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade *(12)*		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades *(12)*		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	W
		V_{CCIO} = 2.375 V *(13)*	30		80	W

Figure 33. Relationship between V_{CCIO} & V_{CCINT} for 3.3-V PCI Compliance

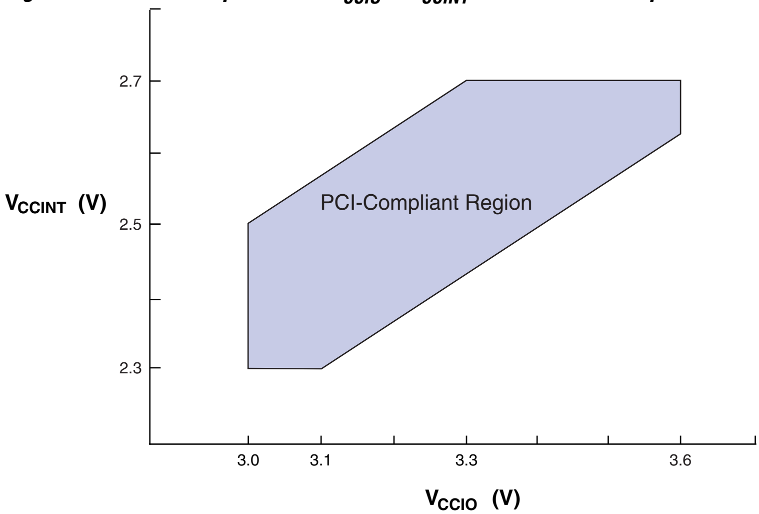
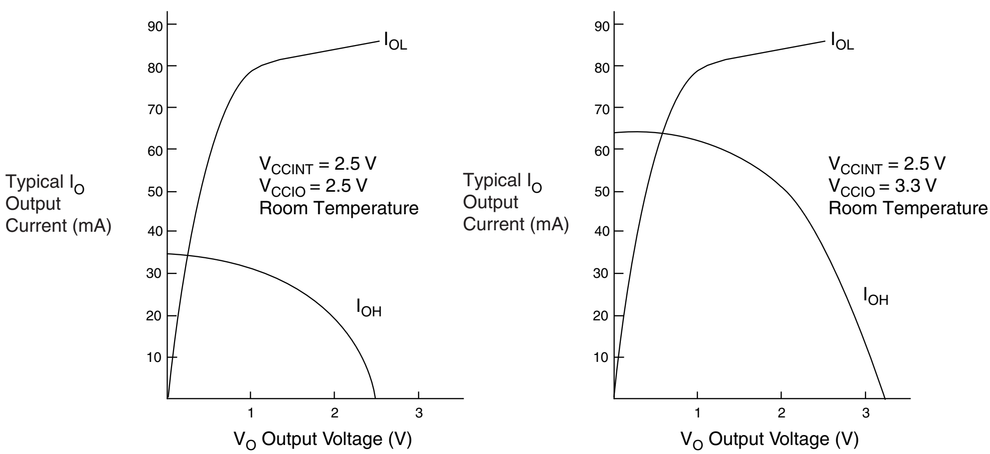


Figure 34 shows the typical output drive characteristics of APEX 20K devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compatible with the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (when VCCIO pins are connected to 3.3 V). 5-V tolerant APEX 20K devices in the -1 speed grade are 5-V PCI compliant over all operating conditions.

Figure 34. Output Drive Characteristics of APEX 20K Device *Note (1)*



Note to Figure 34:

(1) These are transient (AC) currents.

Table 41. EP20K200 f_{MAX} Timing Parameters							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.7		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.4		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Table 52. EP20K30E Minimum Pulse Width Timing Parameters							
Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	0.55		0.78		1.15		ns
t_{CL}	0.55		0.78		1.15		ns
t_{CLRP}	0.22		0.31		0.46		ns
t_{PREP}	0.22		0.31		0.46		ns
t_{ESBCH}	0.55		0.78		1.15		ns
t_{ESBCL}	0.55		0.78		1.15		ns
t_{ESBWP}	1.43		2.01		2.97		ns
t_{ESBRP}	1.15		1.62		2.39		ns

Table 53. EP20K30E External Timing Parameters							
Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.02		2.13		2.24		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.88	2.00	5.36	2.00	5.88	ns
$t_{INSUPLL}$	2.11		2.23		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.60	0.50	2.88	-	-	ns

Table 54. EP20K30E External Bidirectional Timing Parameters							
Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.85		1.77		1.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.88	2.00	5.36	2.00	5.88	ns
$t_{XZBIDIR}$		7.48		8.46		9.83	ns
$t_{ZXBIDIR}$		7.48		8.46		9.83	ns
$t_{INSUBIDIRPLL}$	4.12		4.24		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.60	0.50	2.88	-	-	ns
$t_{XZBIDIRPLL}$		5.21		5.99		-	ns
$t_{ZXBIDIRPLL}$		5.21		5.99		-	ns

Tables 67 through 72 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K160E APEX 20KE devices.

Table 67. EP20K160E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.22		0.24		0.26		ns
t_{H}	0.22		0.24		0.26		ns
t_{CO}		0.25		0.31		0.35	ns
t_{LUT}		0.69		0.88		1.12	ns

Table 68. EP20K160E f_{MAX} ESB Timing Microparameters							
Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.65		2.02		2.11	ns
t_{ESBSRC}		2.21		2.70		3.11	ns
t_{ESBAWC}		3.04		3.79		4.42	ns
t_{ESBSWC}		2.81		3.56		4.10	ns
$t_{ESBWASU}$	0.54		0.66		0.73		ns
t_{ESBWAH}	0.36		0.45		0.47		ns
$t_{ESBWDSU}$	0.68		0.81		0.94		ns
t_{ESBWDH}	0.36		0.45		0.47		ns
$t_{ESBRASU}$	1.58		1.87		2.06		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.41		1.71		2.00		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.02		-0.03		0.09		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.14		0.17		0.35		ns
$t_{ESBRADDRSU}$	0.21		0.27		0.43		ns
$t_{ESBDATACO1}$		1.04		1.30		1.46	ns
$t_{ESBDATACO2}$		2.15		2.70		3.16	ns
t_{ESBDD}		2.69		3.35		3.97	ns
t_{PD}		1.55		1.93		2.29	ns
$t_{PTERMSU}$	1.01		1.23		1.52		ns
$t_{PTERMCO}$		1.06		1.32		1.04	ns

Table 86. EP20K400E f_{MAX} ESB Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.67		1.91		1.99	ns
t_{ESBSRC}		2.30		2.66		2.93	ns
t_{ESBAWC}		3.09		3.58		3.99	ns
t_{ESBSWC}		3.01		3.65		4.05	ns
$t_{ESBWASU}$	0.54		0.63		0.65		ns
t_{ESBWAH}	0.36		0.43		0.42		ns
$t_{ESBWDSU}$	0.69		0.77		0.84		ns
t_{ESBWDH}	0.36		0.43		0.42		ns
$t_{ESBRASU}$	1.61		1.77		1.86		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.35		1.47		1.61		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.18		-0.30		-0.27		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	-0.02		-0.11		-0.03		ns
$t_{ESBRADDRSU}$	0.06		-0.01		-0.05		ns
$t_{ESBDATACO1}$		1.16		1.40		1.54	ns
$t_{ESBDATACO2}$		2.18		2.55		2.85	ns
t_{ESBDD}		2.73		3.17		3.58	ns
t_{PD}		1.57		1.83		2.07	ns
$t_{PTERMSU}$	0.92		0.99		1.18		ns
$t_{PTERMCO}$		1.18		1.43		1.17	ns

Table 87. EP20K400E f_{MAX} Routing Delays

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.25		0.26	ns
t_{F5-20}		1.01		1.12		1.25	ns
t_{F20+}		3.71		3.92		4.17	ns

Table 88. EP20K400E Minimum Pulse Width Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	1.36		2.22		2.35		ns
t_{CL}	1.36		2.26		2.35		ns
t_{CLRP}	0.18		0.18		0.19		ns
t_{PREP}	0.18		0.18		0.19		ns
t_{ESBCH}	1.36		2.26		2.35		ns
t_{ESBCL}	1.36		2.26		2.35		ns
t_{ESBWP}	1.17		1.38		1.56		ns
t_{ESBRP}	0.94		1.09		1.25		ns

Table 89. EP20K400E External Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.51		2.64		2.77		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{INSUPLL}$	3.221		3.38		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.25	0.50	2.45	-	-	ns

Tables 97 through 102 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1000E APEX 20KE devices.

Table 97. EP20K1000E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.25		0.25		ns
t_H	0.25		0.25		0.25		ns
t_{CO}		0.28		0.32		0.33	ns
t_{LUT}		0.80		0.95		1.13	ns

Table 102. EP20K1000E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	3.22		3.33		3.51		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.75	2.00	6.33	2.00	6.90	ns
$t_{XZBIDIR}$		6.31		7.09		7.76	ns
$t_{ZXBIDIR}$		6.31		7.09		7.76	ns
$t_{INSUBIDIRPLL}$	3.25		3.26				ns
$t_{INHBIDIRPLL}$	0.00		0.00				ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.99			ns
$t_{XZBIDIRPLL}$		2.81		3.80			ns
$t_{ZXBIDIRPLL}$		2.81		3.80			ns

Tables 103 through 108 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K1500E APEX 20KE devices.

Table 103. EP20K1500E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.25		0.25		0.25		ns
t_H	0.25		0.25		0.25		ns
t_{CO}		0.28		0.32		0.33	ns
t_{LUT}		0.80		0.95		1.13	ns

Revision History

The information contained in the *APEX 20K Programmable Logic Device Family Data Sheet* version 5.1 supersedes information published in previous versions.

Version 5.1

APEX 20K Programmable Logic Device Family Data Sheet version 5.1 contains the following changes:

- In version 5.0, the VI input voltage spec was updated in Table 28 on page 63.
- In version 5.0, *Note (5)* to Tables 27 through 30 was revised.
- Added *Note (2)* to Figure 21 on page 33.

Version 5.0

APEX 20K Programmable Logic Device Family Data Sheet version 5.0 contains the following changes:

- Updated Tables 23 through 26. Removed 2.5-V operating condition tables because all APEX 20K devices are now 5.0-V tolerant.
- Updated conditions in Tables 33, 38 and 39.
- Updated data for $t_{ESBDATAH}$ parameter.

Version 4.3

APEX 20K Programmable Logic Device Family Data Sheet version 4.3 contains the following changes:

- Updated Figure 20.
- Updated *Note (2)* to Table 13.
- Updated notes to Tables 27 through 30.

Version 4.2

APEX 20K Programmable Logic Device Family Data Sheet version 4.2 contains the following changes:

- Updated Figure 29.
- Updated *Note (1)* to Figure 29.